



ALPHA & OMEGA
SEMICONDUCTOR



AOD607

Complementary Enhancement Mode Field Effect Transistor

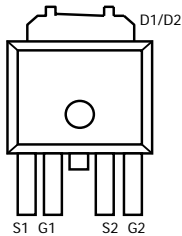
General Description

The AOD607 uses advanced trench technology MOSFETs to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs may be used in H-bridge, Inverters and other applications. *Standard product AOD607 is Pb free (meets ROHS & Sony 259 specifications). AOD607L is a Green Product ordering option. AOD607 and AOD607L are electrically identical.*

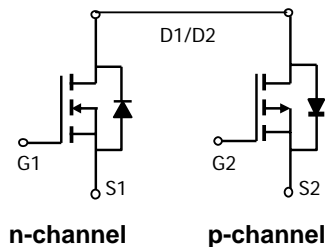
Features

n-channel	p-channel
$V_{DS} (V) = 30V$	-30V
$I_D = 12A (V_{GS}=10V)$	-12A ($V_{GS} = -10V$)
$R_{DS(ON)}$	$R_{DS(ON)}$
< 25 m Ω ($V_{GS}=10V$)	< 37 m Ω ($V_{GS} = -10V$)
< 34 m Ω ($V_{GS}=4.5V$)	< 62 m Ω ($V_{GS} = -4.5V$)

TO-252-4L
D-PAK



Top View
Drain Connected to
Tab



n-channel

p-channel

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Max n-channel	Max p-channel	Units
Drain-Source Voltage	V_{DS}	30	-30	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Continuous Drain Current ^G	I_D	12	-12	A
$T_C=25^\circ\text{C}$				
$T_C=100^\circ\text{C}$				
Pulsed Drain Current ^C	I_{DM}	40	-40	
Avalanche Current ^C	I_{AR}	18	-18	A
Repetitive avalanche energy $L=0.1\text{mH}$ ^C	E_{AR}	40	40	mJ
Power Dissipation ^B	P_D	25	25	W
		$T_C=25^\circ\text{C}$		
$T_C=100^\circ\text{C}$		12.5	12.5	
Power Dissipation ^A	P_{DSM}	2.1	2.1	W
		$T_A=25^\circ\text{C}$		
$T_A=70^\circ\text{C}$		1.3	1.3	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	-55 to 175	$^\circ\text{C}$

Thermal Characteristics: n-channel and p-channel

Parameter	Symbol	Device	Typ	Max	
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	n-ch	19	23	$^\circ\text{C/W}$
$t \leq 10\text{s}$					
Maximum Junction-to-Ambient ^A		n-ch	47	60	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	p-ch	19	23	$^\circ\text{C/W}$
$t \leq 10\text{s}$					
Maximum Junction-to-Ambient ^A		p-ch	47	60	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	p-ch	19	23	$^\circ\text{C/W}$
$t \leq 10\text{s}$					
Maximum Junction-to-Ambient ^A		p-ch	47	60	$^\circ\text{C/W}$
Maximum Junction-to-Case ^B	$R_{\theta JC}$	n-ch	4.5	6	$^\circ\text{C/W}$
Steady-State					
Maximum Junction-to-Case ^B		p-ch	4.5	6	$^\circ\text{C/W}$
Steady-State					

N-Channel Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=24\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1	1.7	2.5	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$, $V_{DS}=5\text{V}$	40			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=12\text{A}$ $T_J=125^\circ\text{C}$		20 28	25 34	m Ω
		$V_{GS}=4.5\text{V}$, $I_D=5\text{A}$		27.5	34	m Ω
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=12\text{A}$		25		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.75	1	V
I_S	Maximum Body-Diode Continuous Current				18	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance			1040	1250	pF
C_{oss}	Output Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		180		pF
C_{rss}	Reverse Transfer Capacitance			110		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		0.7	1.5	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge			19.8	25	nC
$Q_g(4.5\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $I_D=12\text{A}$		9.8	12.5	nC
Q_{gs}	Gate Source Charge			2.5		nC
Q_{gd}	Gate Drain Charge			3.5		nC
$t_{D(on)}$	Turn-On Delay Time			4.5		ns
t_r	Turn-On Rise Time	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=1.25\Omega$,		3.9		ns
$t_{D(off)}$	Turn-Off Delay Time	$R_{GEN}=3\Omega$		17.4		ns
t_f	Turn-Off Fall Time			3.2		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=12\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		19	25	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=12\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		8		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

B: The power dissipation P_D is based on $T_{J(MAX)}=175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=175^\circ\text{C}$.

D: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E: The static characteristics in Figures 1 to 6 are obtained using $<300 \mu\text{s}$ pulses, duty cycle 0.5% max.

F: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

G: The maximum current rating is limited by bond-wires.

Rev 0: March 2006

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

N-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

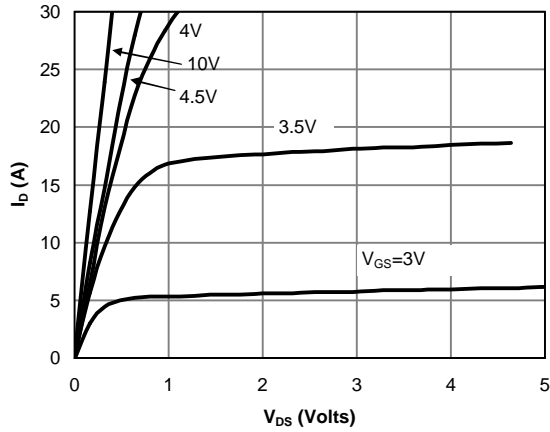


Fig 1: On-Region Characteristics

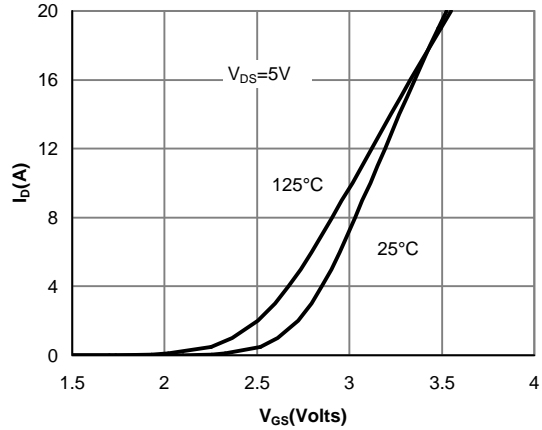


Figure 2: Transfer Characteristics

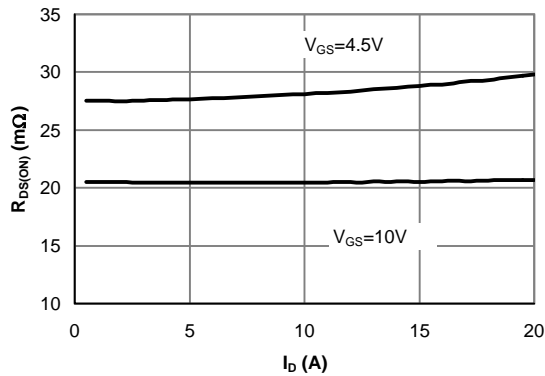


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

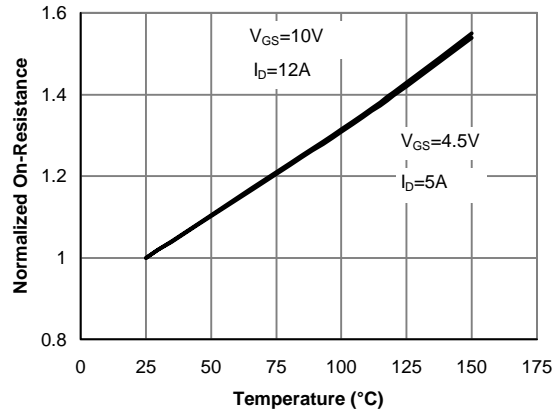


Figure 4: On-Resistance vs. Junction Temperature

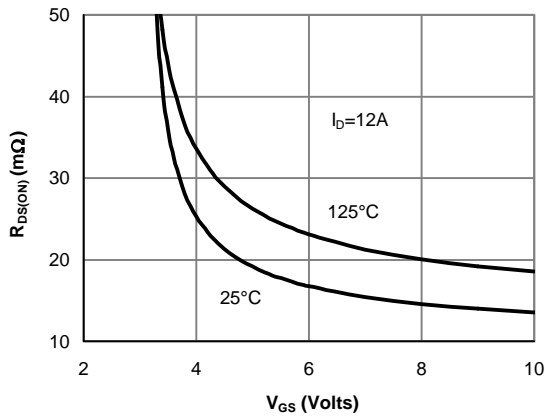


Figure 5: On-Resistance vs. Gate-Source Voltage

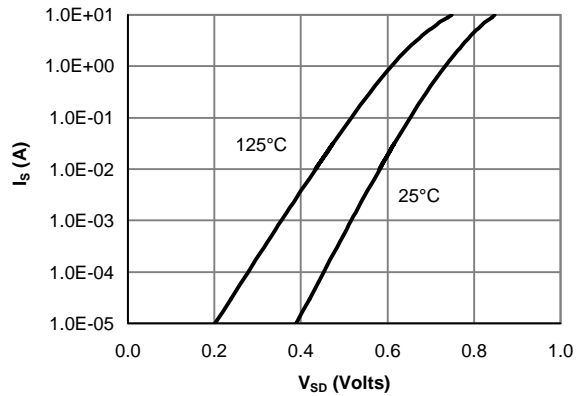


Figure 6: Body-Diode Characteristics

N-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

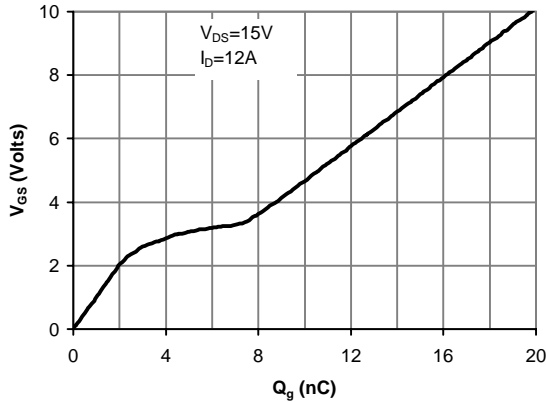


Figure 7: Gate-Charge Characteristics

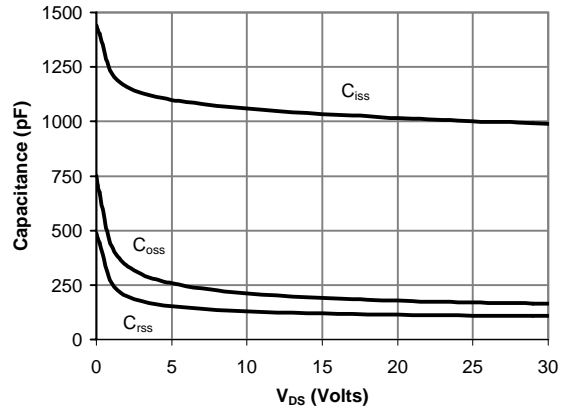


Figure 8: Capacitance Characteristics

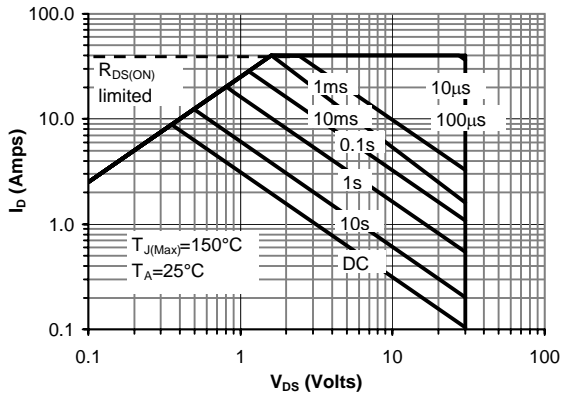


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

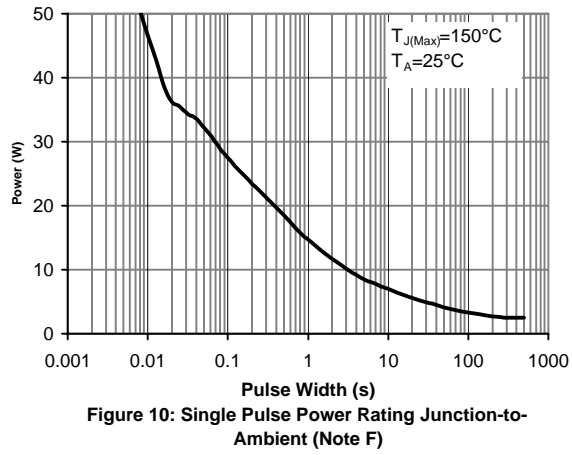


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

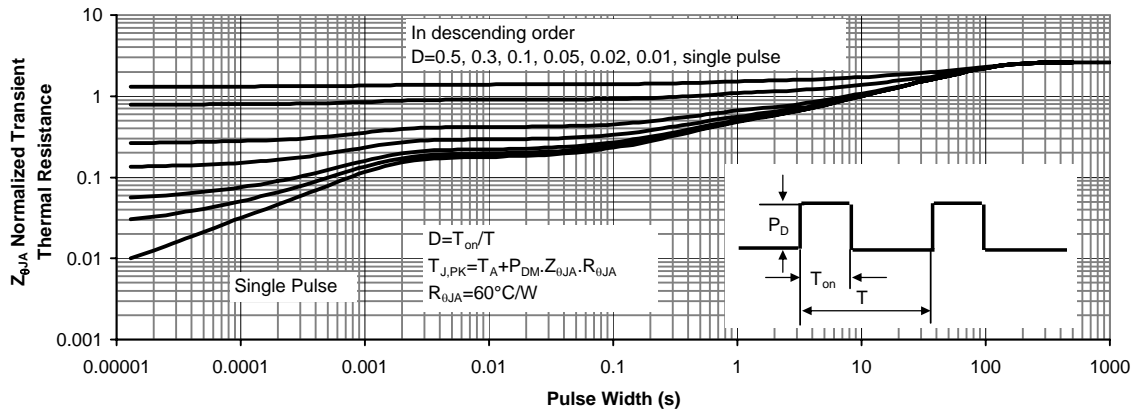


Figure 11: Normalized Maximum Transient Thermal Impedance

P-Channel Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-24\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$		-0.003	-1	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$	-1.2	-2	-2.4	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-10\text{V}$, $V_{DS}=-5\text{V}$	-40			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}$, $I_D=-12\text{A}$ $T_J=125^\circ\text{C}$		30	37	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}$, $I_D=-5\text{A}$		42	50	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}$, $I_D=-12\text{A}$		17		S
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}$, $V_{GS}=0\text{V}$		-0.76	-1	V
I_S	Maximum Body-Diode Continuous Current				-18	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=-15\text{V}$, $f=1\text{MHz}$		920	1100	pF
C_{oss}	Output Capacitance			190		pF
C_{rss}	Reverse Transfer Capacitance			122		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		3.6	5	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge (10V)	$V_{GS}=-10\text{V}$, $V_{DS}=-15\text{V}$, $I_D=-12\text{A}$		18.7	23	nC
$Q_g(4.5\text{V})$	Total Gate Charge (4.5V)			9.7	11.7	nC
Q_{gs}	Gate Source Charge			2.54		nC
Q_{gd}	Gate Drain Charge			5.4		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=-10\text{V}$, $V_{DS}=-15\text{V}$, $R_L=1.25\Omega$, $R_{GEN}=3\Omega$		9	13	ns
t_r	Turn-On Rise Time			25	35	ns
$t_{D(off)}$	Turn-Off DelayTime			20	30	ns
t_f	Turn-Off Fall Time			12	18	ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-12\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		21.4	26	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-12\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		13	16	nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The Power dissipation P_{DSM} is based on steady-state $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB or heatsink allows it.

B: The power dissipation P_D is based on $T_{J(MAX)}=175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

C: Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=175^\circ\text{C}$.

D: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E: The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

F: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

G: The maximum current rating is limited by the package current capability.

Rev0 : March 2006

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE

P-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

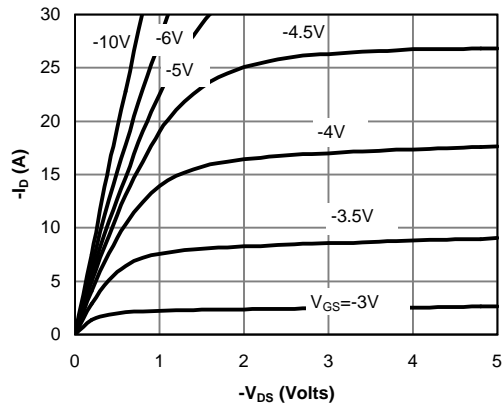


Fig 1: On-Region Characteristics

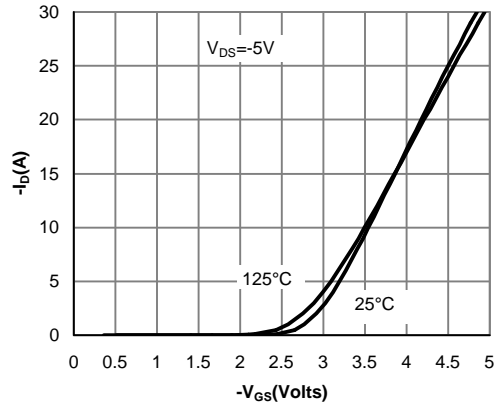


Figure 2: Transfer Characteristics

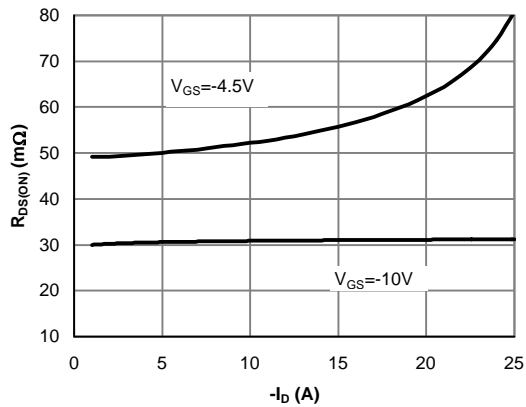


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

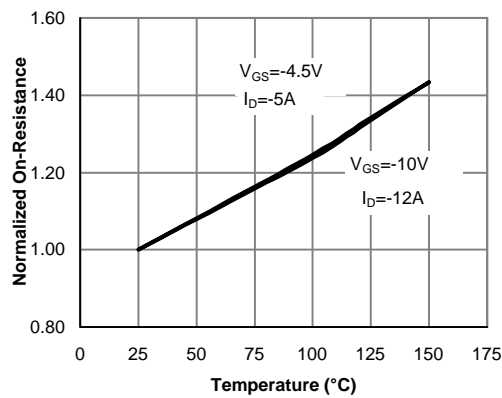


Figure 4: On-Resistance vs. Junction Temperature

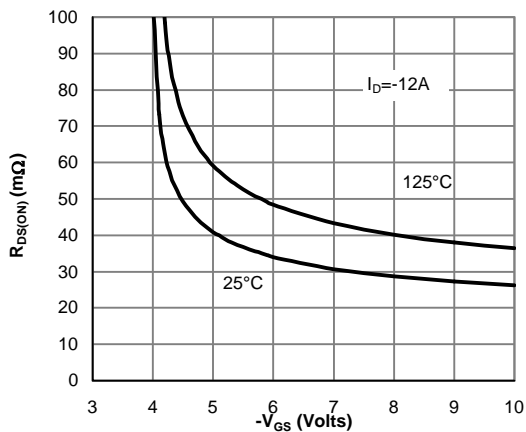


Figure 5: On-Resistance vs. Gate-Source Voltage

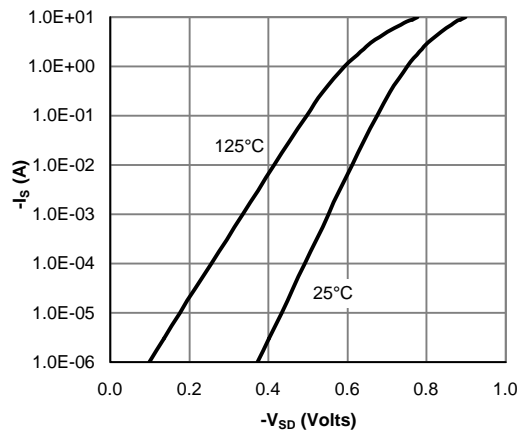


Figure 6: Body-Diode Characteristics

P-CHANNEL TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

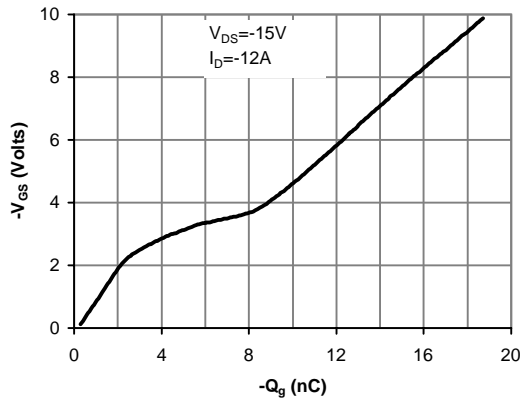


Figure 7: Gate-Charge Characteristics

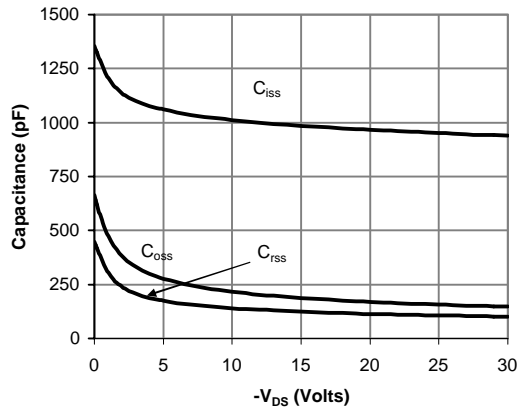


Figure 8: Capacitance Characteristics

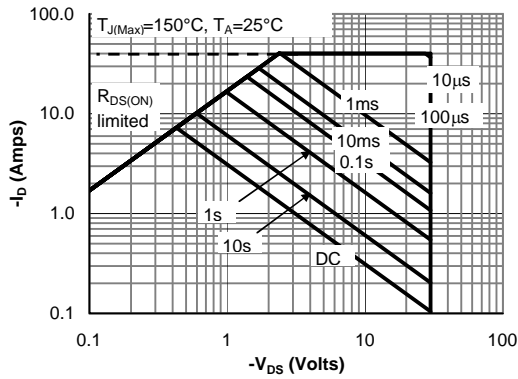


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

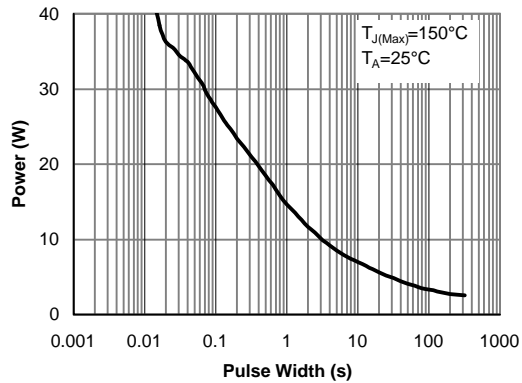


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

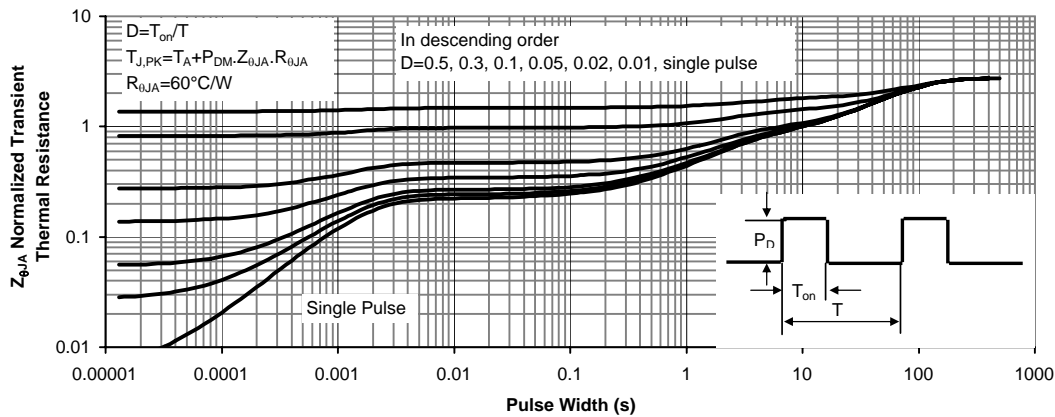


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)